

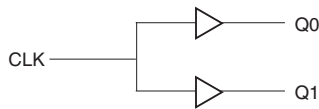
GENERAL DESCRIPTION

The 8302I is a low skew, 1-to-2 LVCMOS Fanout Buffer. The 8302I has a single ended clock input. The single ended clock input accepts LVCMOS or LVTTTL input levels. The 8302I features a pair of LVCMOS outputs. The 8302I is characterized at full 3.3V for input V_{DD} , and mixed 3.3V and 2.5V for output operating supply modes (V_{DDO}). Guaranteed output and part-to-part skew characteristics make the 8302I ideal for clock distribution applications demanding well defined performance and repeatability.

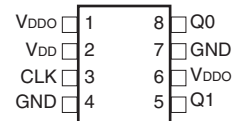
FEATURES

- 2 LVCMOS / LVTTTL outputs
- LVCMOS / LVTTTL clock input accepts LVCMOS or LVTTTL input levels
- Maximum output frequency: 200MHz
- Output skew: 40ps (typical)
- Part-to-part skew: 250ps (typical)
- Small 8 lead SOIC package saves board space
- Full 3.3V or 3.3V core, 2.5V supply modes
- -40°C to 85°C ambient operating temperature
- Lead-Free package fully RoHS compliant

BLOCK DIAGRAM



PIN ASSIGNMENT



8302I
8-Lead SOIC
 3.8mm x 4.8mm, x 1.47mm package body
M Package
 Top View

TABLE 1. PIN DESCRIPTIONS

| Number | Name | Type | | Description |
|--------|------------------|--------|----------|---|
| 1, 6 | V _{DDO} | Power | | Output supply pins. |
| 2 | V _{DD} | Power | | Core supply pin. |
| 3 | CLK | Input | Pulldown | LVC MOS / LV TTL clock input. |
| 4,7 | GND | Power | | Power supply ground. |
| 5 | Q1 | Output | | Single clock output. LVC MOS / LV TTL interface levels. |
| 8 | Q0 | Output | | Single clock output. LVC MOS / LV TTL interface levels. |

NOTE: *Pulldown* refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|--|---|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | | | 4 | | pF |
| C _{PD} | Power Dissipation Capacitance (per output) | V _{DD} , V _{DDO} = 3.465V | | 22 | | pF |
| | | V _{DD} = 3.465V, V _{DDO} = 2.625V | | 16 | | pF |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |
| R _{OUT} | Output Impedance | | | 7 | | Ω |

ABSOLUTE MAXIMUM RATINGS

| | |
|--|---------------------------|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, V_O | -0.5V to $V_{DDO} + 0.5V$ |
| Package Thermal Impedance, θ_{JA} | 112.7°C/W (0 lfpm) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 3A. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDO} | Output Power Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| I_{DD} | Power Supply Current | | | | 14 | mA |
| I_{DDO} | Output Supply Current | | | | 5 | mA |

TABLE 3B. POWER SUPPLY DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|-----------------|---------|---------|---------|-------|
| V_{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDO} | Output Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I_{DD} | Power Supply Current | | | | 14 | mA |
| I_{DDO} | Output Supply Current | | | | 5 | mA |

TABLE 3C. LVCMOS / LVTTTL DC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|---------------------|---------------------------------------|---------|---------|----------------|---------------|
| V_{IH} | Input High Voltage | | 2 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | | -0.3 | | 1.3 | V |
| I_{IH} | Input High Current | CLK $V_{DD} = V_{IN} = 3.465V$ | | | 150 | μA |
| I_{IL} | Input Low Current | CLK $V_{DD} = 3.465V, V_{IN} = 0V$ | -5 | | | μA |
| V_{OH} | Output High Voltage | 50Ω to $V_{DDO}/2$ | 2.6 | | | V |
| | | $I_{OH} = -100\mu\text{A}$ | 2.9 | | | V |
| V_{OL} | Output Low Voltage | 50Ω to $V_{DDO}/2$ | | | 0.5 | V |
| | | $I_{OL} = 100\mu\text{A}$ | | | 0.2 | V |

TABLE 3D. LVCMOS / LVTTTL DC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|---------------------|---------------------------------------|---------|---------|----------------|---------------|
| V_{IH} | Input High Voltage | | 2 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | | -0.3 | | 1.3 | V |
| I_{IH} | Input High Current | CLK $V_{DD} = V_{IN} = 3.465V$ | | | 150 | μA |
| I_{IL} | Input Low Current | CLK $V_{DD} = 3.465V, V_{IN} = 0V$ | -5 | | | μA |
| V_{OH} | Output High Voltage | 50Ω to $V_{DDO}/2$ | 1.8 | | | V |
| | | $I_{OH} = -100\mu\text{A}$ | 2.2 | | | V |
| V_{OL} | Output Low Voltage | 50Ω to $V_{DDO}/2$ | | | 0.5 | V |
| | | $I_{OL} = 100\mu\text{A}$ | | | 0.2 | V |

TABLE 4A. AC CHARACTERISTICS, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------------|--|--|---------|---------|---------|-------|
| f_{MAX} | Output Frequency | | | | 200 | MHz |
| t_{pLH} | Propagation Delay, Low-to-High; NOTE 1 | $f \leq 200\text{MHz}$ | 1.9 | 2.35 | 2.8 | ns |
| $t_{sk(o)}$ | Output Skew; NOTE 2, 4 | | | 40 | 105 | ps |
| $t_{sk(pp)}$ | Part-to-Part Skew; NOTE 3, 4 | | | 250 | 800 | ps |
| t_R | Output Rise Time | 20% to 80% | 300 | | 800 | ps |
| t_F | Output Fall Time | 20% to 80% | 300 | | 800 | ps |
| odc | Output Duty Cycle | $f \leq 133\text{MHz}$ | 45 | | 55 | % |
| | | $133\text{MHz} < f \leq 200\text{MHz}$ | 40 | | 60 | % |

Parameters measured at f_{MAX} unless otherwise noted.

NOTE 1: Measured from $V_{DD}/2$ of the input to $V_{DDO}/2$ of the output.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at $V_{DDO}/2$.

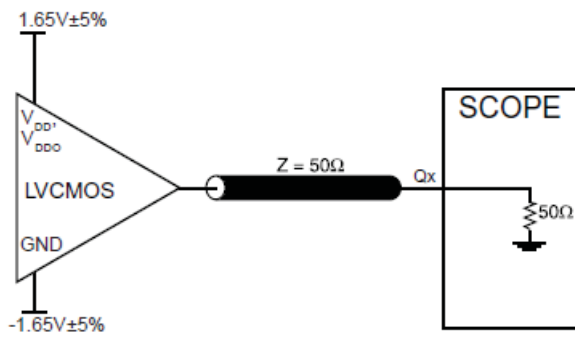
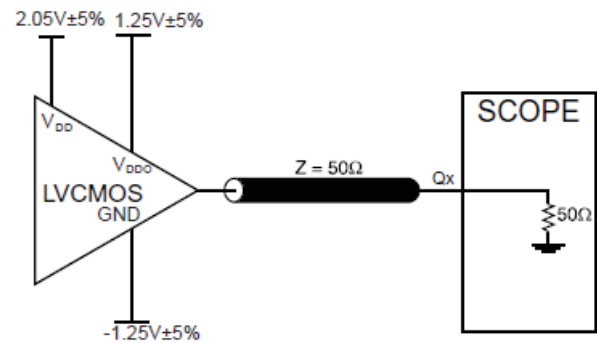
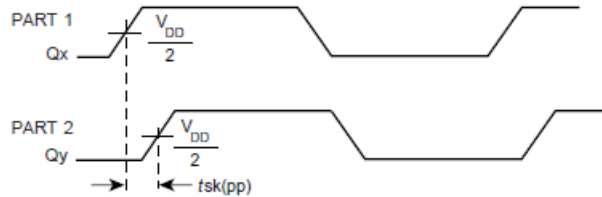
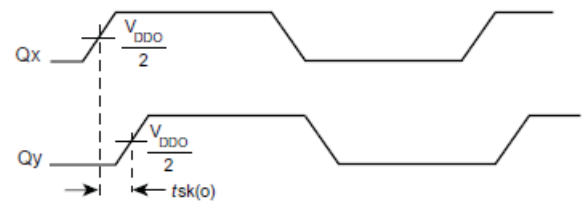
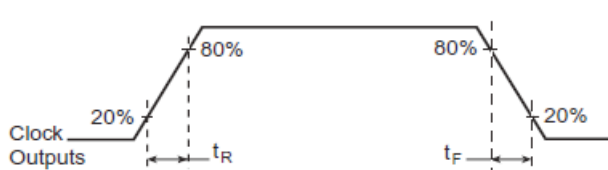
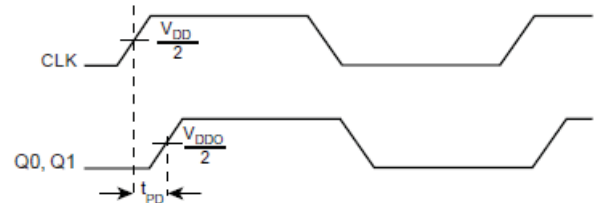
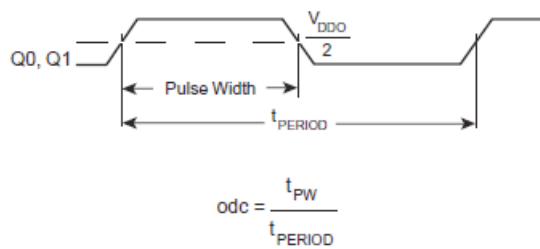
NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

TABLE 4B. AC CHARACTERISTICS, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------------|--|--|---------|---------|---------|-------|
| f_{MAX} | Output Frequency | | | | 200 | MHz |
| t_{pLH} | Propagation Delay, Low-to-High; NOTE 1 | $f \leq 200\text{MHz}$ | 2.3 | | 3.3 | ns |
| $t_{sk(o)}$ | Output Skew; NOTE 2, 4 | | | | 110 | ps |
| $t_{sk(pp)}$ | Part-to-Part Skew; NOTE 3, 4 | | | 250 | 800 | ps |
| t_R | Output Rise Time | 20% to 80% | 250 | | 650 | ps |
| t_F | Output Fall Time | 20% to 80% | 250 | | 650 | ps |
| odc | Output Duty Cycle | $f \leq 133\text{MHz}$ | 45 | | 55 | % |
| | | $133\text{MHz} < f \leq 200\text{MHz}$ | 40 | | 60 | % |

See Table 4A above for notes.

PARAMETER MEASUREMENT INFORMATION


3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT

3.3V CORE/2.5V OUTPUT LOAD AC TEST CIRCUIT

PART-TO-PART SKEW

OUTPUT SKEW

OUTPUT RISE/FALL TIME

PROPAGATION DELAY

OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD

RELIABILITY INFORMATION

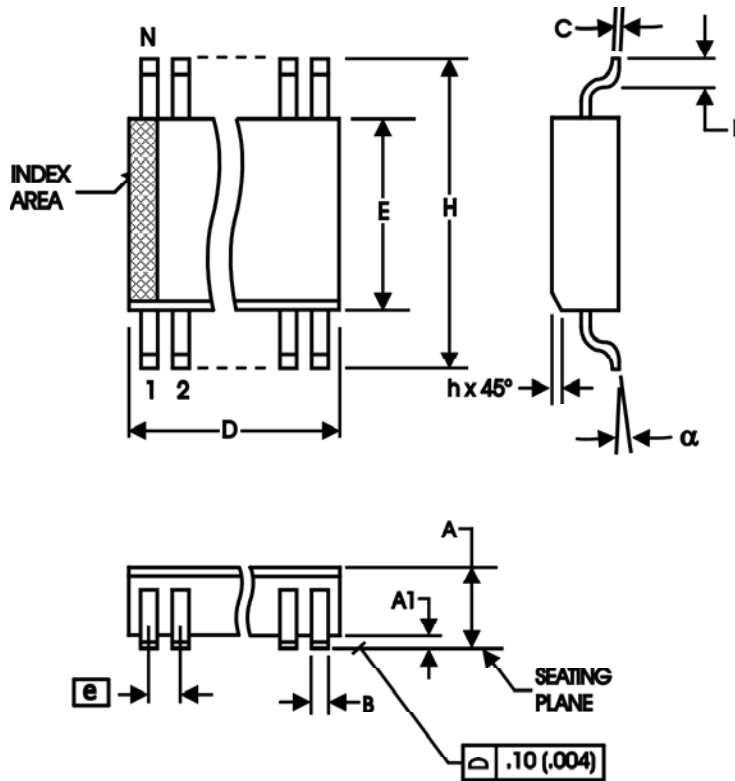
TABLE 5. θ_{JA} VS. AIR FLOW TABLE FOR 8 LEAD SOIC

| θ_{JA} by Velocity (Linear Feet per Minute) | | | |
|--|-----------|-----------|-----------|
| | 0 | 200 | 500 |
| Single-Layer PCB, JEDEC Standard Test Boards | 153.3°C/W | 128.5°C/W | 115.5°C/W |
| Multi-Layer PCB, JEDEC Standard Test Boards | 112.7°C/W | 103.3°C/W | 97.1°C/W |

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

TRANSISTOR COUNT

The transistor count for 8302I is: 322

PACKAGE OUTLINE - SUFFIX M FOR 8 LEAD SOIC

TABLE 6. PACKAGE DIMENSIONS

| SYMBOL | Millimeters | |
|----------|-------------|---------|
| | MINIMUM | MAXIMUM |
| N | 8 | |
| A | 1.35 | 1.75 |
| A1 | 0.10 | 0.25 |
| B | 0.33 | 0.51 |
| C | 0.19 | 0.25 |
| D | 4.80 | 5.00 |
| E | 3.80 | 4.00 |
| e | 1.27 BASIC | |
| H | 5.80 | 6.20 |
| h | 0.25 | 0.50 |
| L | 0.40 | 1.27 |
| α | 0° | 8° |

Reference Document: JEDEC Publication 95, MS-012

TABLE 7. ORDERING INFORMATION

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|--------------------------|----------------|-------------------------|---------------------------|--------------------|
| 8302AMILF | 8302AMIL | 8 lead "Lead Free" SOIC | Tube | -40°C to +85°C |
| 8302AMILFT | 8302AMIL | 8 lead "Lead Free" SOIC | Tape and Reel | -40°C to +85°C |

| REVISION HISTORY SHEET | | | | |
|------------------------|-------|---------|--|---------|
| Rev | Table | Page | Description of Change | Date |
| A | T7 | 1 8 | Features Section - added Lead-Free bullet. Ordering Information Table - added Lead-Free part number. | 3/24/05 |
| A | T7 | 8 10 | Updated datasheet's header/footer with IDT from ICS. Removed ICS prefix from Part/Order Number column. Added Contact Page. | 7/29/10 |
| A | T7 | 8 | Removed ICS from the part numbers where needed. Ordering Information - removed quantity from tape and reel. Deleted LF note below table. Updated data sheet header and footer. | 3/4/16 |



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